1. The Coulomb force is:

(a)
$$F = K \frac{q_1 q_2}{r^2}$$

 $q_1 q_2$

(b)
$$F = K \frac{q_1 q_2}{r}$$

(c)
$$F = K_{r^3}$$

(d) $F = K_{Q_2}$

(b)

- 2. The value of K depends upon:
 - Charges
 - (c) The distance between charges

The value of K in SI system of units:

- System of units and medium Nature of medium **(d)**
- 3.
- (a) $9 \times 10^9 \text{ Nm}^2/\text{c}^2$

(b) $9 \times 10^{10} \text{ Nm}^2/\text{c}^2$

(c) $9 \times 10^{-9} \text{ Nm}^2/\text{c}^2$

- (d) $9 \times 10^9 \,\text{NC/m}^2$
- The branch of physics which deals with the charges at rest: 4.
 - Current electricity

(b) Electromagnetism

(c) **Electrostatics**

- (d) Nuclear physics
- The value of permitivity of free space: 5.
 - (a) $8.85 \times 10^{-12} \,\mathrm{C}^2/\mathrm{Nm}^2$

(b) $8.85 \times 10^{-12} \,\mathrm{C}^2 \mathrm{m}^2 / \mathrm{N}$

 $8.85 \times 10^{-12} \text{ Nm}^2/\text{C}$

- (d) $8.85 \times 10^{-11} \text{ Nm}^2/\text{C}^2$
- 6. When the medium is insulator the electrostatic force between the charges is:
 - Decreased (a)

(b) Zero

(c) Increased

- None of above
- 7. What is standard to measure the relative permitivity:
 - (a) Water

Vacuum **(b)**

(c) Air

- (d) Atmosphere
- 8. Which of the following statement is correct:
 - (a) Similar charges attract each other
- **(b)** Similar charges attract and repel each other
- (c) Similar charges repel each other
- (d) Similar charges neither attract nor repel
- 9. Metals are good conductors of electricity because they have:
 - Large number of bounded electrons (a)
- **(b)** Small number of electrons

	(c)	Large number of free electrons	(d)	Small number of free electrons
10.	Free	e electrons are:		
	(a)	Fixed	(b)	Loosely bounded
	(c)	Strongly fixed	(d)	Tightly bound
11.	The	SI unit of charge is:		
	(a)	Coulomb	(b)	Calorie
	(c)	Ampere	(d)	Joule
12.	The	number of electrons in one coulomb ch	arge i	s equal to:
	(a)	6.2×10^{18} electrons	(b)	Zero electrons
	(c)	1.6×10^{-22} electrons	(d)	6.2×10^{21} electrons
13.	The	electrostatic force of repulsion between	ı two	electrons at 1 metre is:
	(a)	$9 \times 10^9 \text{ N}$	(b)	$1.44 \times 10^{-9} \text{ N}$
	(c)	$2.30 \times 10^{-28} \text{ N}$	(d)	1 N
14.	A cl	narge of 10μC and 14.4 μC are 12 cm ap	part, t	he force between them is:
	(a)	$9 \times 10^5 \mathrm{N}$	(b)	$9 \times 10^7 \text{ N}$
	(c)	90 N	(d)	$108 \times 10^7 \text{ N}$
15.	A su	ibstance contains:		
	(a)	Only positive charge	(b)	Only negative charge
	(c)	Both +ve and -ve charge	(d)	None of above
16.	If th	e distance between the two charge bodi	es is l	nalved, the force between them becomes:
	(a)	Half	(b)	Four time
	(c)	One fourth	(d)	Doubled
17.	The	SI units of permitivity are:		
	(a)	$N.m/C^2$	(b)	$C^2/N.m^2$
	(c)	$N.m^2/C^2$	(d)	N.m/C
18.	The	minimum charge on any electron be les	ss thar	n:
	(a)	1.6×10^{-19} C	(b)	3.2×10^{-19} C
	(c)	1.8×10^{-19} C	(d)	9.1×10^{-19} C
19.	The	force in a medium of relative permitivi	$ty \in_r i$	is given by:
	(a)	$F' = \frac{F}{\epsilon_r}$	(b)	$F' = \frac{\epsilon_r}{F}$
	(33)	\in_{r}		-
	(c)	$F' = \in_{\mathrm{r}} \cdot F$	(d)	$F' = \frac{F}{\epsilon_0 \epsilon_r}$
20.	Whe	en current of one ampere is flowing acro	oss an	y cross-section of wire in one second, then the

(b) Three coulomb

quantity of charge is said to be:

One coulomb

	(c)	One micro-coulomb	(d)	None of above
21.		electric force between two charges pla 80, the force reduced to:	ced ii	n air is 2 Newton. When placed in a medium of
	(a)	0.029 N	(b)	0.025 N
	(c)	0.03 N	(d)	0.04 N
22.	The	value of \in_r for various dielectrics is alw	vays:	
	(a)	Larger than unity	(b)	Less than unity
	(c)	Equal to unity	(d)	None of above
23.	A m will		s char	ged with 4×10^{-8} c. The potential on its surface
	(a)	90 volts	(b)	9 volts
	(c)	9000 volts	(d)	900 volts
24.	Orig	gin of the gravitational and electric force	es:	
	(a)	is still unknown	(b)	was known in 1611 A.D
	(c)	was known in 1712 A.D	(d)	was known in 1911 A.D
25.	Mic	hael Faraday was known by his work or	ı:	
	(a)	Electric force	(b)	Weak nuclear force
	(c)	Strong nuclear force	(d)	Gravitational force
26.	The	SI unit of charge is:		
	(a)	Meter	(b)	Ampere
	(c)	Coulomb	(d)	Volt
27.	In c	ase of two identical charges placed at ce	ertain	distance, the electric lines of force are:
	(a)	Curved	(b)	Straight lines
	(c)	Both (a) and (b)	(d)	None of these
28.	An	example of photoconductor is:		
	(a)	Iron	(b)	Aluminum
	(c)	Carbon	(d)	Selenium
29.	Sele	enium is:		
	(a)	Conductor		
	(b)	Insulator in the dark are becomes cond	ducto	when exposed to light
	(c)	An insulator		
	(d)	None of these		
30.	The	inkjet printer ejects a thin stream of:		
	(a)	Ink	(b)	Water

1	(c)	Oil	(d)	None of these
31.	An i	mportant part of inkjet printer is:		
	(a)	Deflection plates	(b)	Toner
	(c)	Drum	(d)	None of these
32.	An i	nkjet printer uses in its operation:		
	(a)	Positrons	(b)	Neutrons
	(c)	An electric charge	(d)	Photons
33. 9	The	photo copying process is called:		
	(a)	Xerography	(b)	Inkjet printer
	(c)	Both (a) and (b)	(d)	None of these
34. 9	An i	mportant port of a photocopier is:		
	(a)	Deflation plates	(b)	Toner
	(c)	Charging electrode	(d)	Printed head
35. ♀	Xero	ography means:		
	(a)	Dry writing	(b)	Wet writing
	(c)	Both (a) and (b)	(d)	None of these
36.	The	number of electric field lines passing th	rough	a certain element of area is called:
	(a)	Electric lines of force	(b)	Electric intensity
	(c)	Electric flux	(d)	None of these
37.	The	concept of electric field theory was intro	oduce	d by:
	(a)	Kepler	(b)	Newton
	(c)	Dalton	(d)	Michael Faraday
38.	The	space around the charge within which o	ther c	charges are influenced by it is called:
	(a)	Electric field	(b)	Magnetic field
	(c)	Electric flux	(d)	Electric intensity
39.	The	force per unit charge is called:		
	(a)	Electric field	(b)	Electric field intensity
	(c)	Electric potential energy	(d)	Electric potential
40.	The	electric field exist around:		
	(a)	Charges	(b)	On the left side
	(c)	At the –ve charge	(d)	At the +ve charge
41.	The	practical application of electrostatic is:		
	(a)	Photocopier	(b)	X-rays machines

	(c)	Laser				(d)	All o	of above			
42.	The electric field lines emerge from the charges in:										
(a)	Thre	e dimen	sions		(b) Two dimensions						
(c)	One	dimensi	on		(d)	All	of abo	ve			
The	direct	ion of el	ectric in	tensity is:		13					
(a)	Non	mal to th	e field		(b)	Tang	gent to	the field	l		
(c)	Para	llel to th	e field		(d)	Non	e of at	oove			
44.	Whe		eld is stro	ong, the lines	of force	are:					
	(a)	Closer				(b)	Paral				
	(c)	Farther				(d)		f above			
45.	The	electric l	lines of f	force determi	ine the str	ength	of an:				
	(a)	Gravita	ational fi	eld		(b)	Cons	stant field	d		
	(c)	Magne	tic field			(d)	Elect	tric field			
46.	The	electric	intensity	is a:							
	(a)	Scalar	quantity			(b)	Vect	or quant	ity		
	(c)	Physica	al quanti	ty		(d)	None	e of abov	re		
47.	The	unit of e	electric in	ntensity is:							
	(a)	C/m ²				(b)	N/C				
	(c)	Volt –	meter			(d)	Both	(b) and	(c)		
48.	A ch	narge of 2	2 coulon	nb is in a fiel	d of inten	sity 2	N/C. 7	The force	on charge is	S:	
	(a)	$4\;\pi\;N$				(b)	4 N				
	(c)	0 N				(d)	1 N				
49.	The	electric i	intensity	at a distance	e of 1m fr	om the	point	charge i	s 1μC is:		
	(a)	9×10^{9}) N/C			(b)	9 × 1	06 N/C			
	(c)	9×10^{3}	N/C			(d)	9 N/0	C			
	12.5		T -		Answ					1	
1.	(a)		2.	(b)	3.	(8	-	4.	(c)	5.	(a)
6.	(a)		7.	(b)	8.	((9.	(c)	10.	(b)
11.	(a)		12.	(a)	13.	((14.	(c)	15.	(c)
16.	(c)		17.	(b)	18.	(2		19.	(a)	20.	(a)
21.	(b)		22.	(a)	23.	(0		24.	(a)	25.	(a)
26.	(c)		27.	(a)	28.	(0	l)	29.	(b)	30.	(a)
31.	(a)		32.	(c)	33.	(2	ı)	34.	(b)	35.	(a)
36.	(c)		37.	(d)	38.	(8	ı)	39.	(b)	40.	(a)
41.	(a)		42.	(d)	43.	(t)	44.	(a)	45.	(d)

49.

(c)

(b)

(b)

47.

(b)

48.

46.

1. The	current through a metallic conductor is due to the	e m	otion of
a.	free electrons	b.	Protons
c.	Neutrons	d.	still under controversy
2. Res	istance of a conductor depends upon		
a.	nature of conductor	b.	dimension of conductor
c.	physical state of the conductor	d.	all of above
3. A w	vire having very high value of conductance is said	d to	be
a.	very good conductor	b.	moderately good conductor
c.	an insulator	d.	None
	vire of uniform area of cross-section A length L a	ınd r	resistance R is cut into two parts. Resistivity of
a.	remains the same	b.	is doubled
c.	is halved	d.	becomes zero
5. Pro	duction of heat due to an electric current flowing	thro	ough a conductor is given by
a.	Joule effect	b.	Joule Thomsons effect
c.	Comptons effect	d.	None
6. Wh	en same current passes for same time through a t	h	ick and thin wire
a.	more heat is produced in thick wire	b.	more heat is produced in thin wire
c.	no heat is produced in wire	d.	less heat is produced in thick wire
Wh	ree equal resistors connected in series with a sour at will be the power dissipated if the same resistor or m f?		
a.	40 W	b.	90W
c.	100W	d.	120W
8. One	e kilowatt hour is the amount of energy delivered	dur	ing
a .	one second	b .	one day
c.	one minute	d.	one hour
9. The	ermocouples convert		
a.	heat energy into electrical energy	b.	heat energy into light energy
c.	heat energy into mechanical energy	d.	mechanical energy into heat energy
10. Ho	ow much heat does a 40 W bulb generates in one	hou	r?
a	. 144000J	b.	144J
c.	. 1.44J	d.	14J

11. An	immersion heater of 400 watts kept on for 5 hou	rs w	vill consume electrical power of
a.	2KWh	b.	20KWh
c.	6KWh	d.	12KWh
12. Res	istance of a super conductor is		
a.	Finite	b.	Infinite
c.	Zero	d.	changes with every conductor
13. Res	istance of an ideal insulator is		
a.	Infinite	b.	Zero
c.	Finite	d.	depends upon nature
14. Wh	ich one is the best material for making connectin	ıg w	ires?
a.	Iron	b.	Tungsten
c.	Silver	d.	Copper
15. Rec	iprocal of resistivity is called		
a.	Resistance	b.	Inductance
c.	Conductivity	d.	Flexibility
16. Wh	en 2,4 and 6 ohms resistor are connected in para	llel	their resultant equivalent resistance will be
A.	12ohm	b.	11/12ohm
C.	12/11ohm	d.	None
17. Circ	cuit which gives continuously varying potential	is ca	lled
a.	complex network	b.	wheat stone bridge
c.	potential divider	d.	all of above
18. Inte	rnal resistance is the resistance offered by		
a.	source of e m f	b.	Conductor
c.	Resistor	d.	Capacitor
19. The	ere are three bulbs of 60W 100W and 200W which	ch b	ulb has thickest filament.
a.	100W	b.	200W
c.	60W	d.	All
	ee bulbs are rating 40W 60W and 100W designed at brightly if they are connected in series across?		
a.	40 W bulb	b.	60 W blub
c.	100 W blub	d.	all will burn equally brightly
21. The	current in the circuit shown in figure - What wi	ll be	the current in the circuit?
a.	1/45A	b.	1/10A
c.	1/5A	d.	5A
22. Res	istance between points A and B in the circuit sho	own	in figure is
a.	4 ohm	b.	6ohm

c.	10 ohm	d.	8 ohm
	eon flashlight cell with an emf of 1.5V gives a c meter of resistance 0.04?. Internal resistance of t		
a.	0.0004?	b.	0.06?
с.	0.10?	d.	0.13?
24. Res	istance of a wire on increasing its temperature w	vill	
a.	increase with rise in temperature	b.	decrease with rise in temperature
c.	will remain same	d.	depends upon altitude of experimentation
25. Spe	cific resistance of a wire		
a.	will depend on its length	b.	will depend on its radius
с.	will depend on the type of material of the wire	d.	will depend on none of the above
26. An	electric iron is marked 20 volts 500W. The units	s coi	nsumed by it in using if for 24 hours will be
a.	12	b.	24
c.	5	d.	1100
27. In the	he following figure, the terminal potential is		
a.	zero	b.	2V
c.	12V	d.	36V
28. In li	iquids and gases the current is due to the motion	l	
a.	negative charges	b.	positive charges
c.	both negative and positive charges	d.	neutral particles
29. If 1	ampere current flows through 2m long conductor	or th	e charge flow through it in 1 hour will be
a.	3600C	b.	7200C
c.	1C	d.	2C
30. The	graphical representation of Ohms law is		
a.	hyperbola	b.	Ellipse
c.	parabola	d.	straight line
31. SI u	unit of resistivity is		
a .	ohm	b .	Ohm×m
c.	Ohm×m ⁻¹	d.	Ohm×m ²
32. Wh	ich one of the following materials is useful for n	naki	ng bulb filaments?
a.	aluminum	b.	Iron
c.	Copper	d.	Tungsten
33. The	e resistance of a conductor at absolute zero (OK)	is	

a. zero almost

b. infinite almost

c.	May increase or decrease		d.	None		
34. Wh	y should a resistance be intro	duced in a circuit in	n se	ries deliberately?		
	to increase current			to decrease current		
c.	to control current		d.	just to give a good look to c	ircu	it
35. Ele	ctrical energy is measured in					
	watt		b .	horse power		
c.	kilo watt		d.	kilowatt hour		
36. All to g	• •	nected in parallel to	eac	h other between the main line	e an	d neutral wire
a.	same current		b.	same current and potential c	liffe	erence
c.	different current but same p	ootential	d.	different current and potenti	al d	lifferences
37. Ele	ctrical energy is converted to	heat at the rate of				
a.	IRt		b.	I^2R		
c.	I^2Rt		d.	VIt		
38. Wh	ich one of the following bulb	s has the least resis	tanc	ee?		
a.	100 watt			200 watt		
c.	300 watt		d.	60 watt		
39. A f	use is placed in series with th	e cireuit to protect a	agai	nst		
a.	high power	1	_	high voltage		
c.	high current		d.	over heating		
40. Ter	minal potential difference of	a battery is greater	thar	its emf when		
a.	the internal resistance of ba	ttery is infinite	b.	the internal resistance of bat	tery	is zero
c.	the battery is charged		d.	the battery is discharged		
	Thermistor with high negative temperature especially near i	<u>-</u>	ficie	ent are very accurate for meas	urin	ng low
	a. 10 K	b. 70K		c. 200K	d.	35K
	The resistivity of decrease		e in			
	a. gold Three resistors of resistance	b. silver	vori	c. copper ous ways, which of the follow	d.	silicon
	obtained?	K are connected in	vari	ous ways, which of the follow	/IIIg	camot be
	a. 3R ohm	b. 2R/4 ohm		c. R/3 ohm	d.	2R/3 ohm
	The conventional current is c				.1	1 41. 1 1 .
	 a. atoms and molecules Kirchhoff 1st law is is manife 	 b. positive charge estation of 	es	c. negative charges	a.	both b and c
	a. law of conservation of mas			b. law of conservation of ch	arge	e
	c. law of conservation of en			d. none		
46.	Heat energy is converted into			1	1	
47.	a. solar cells The color code of green is	b. thermocouples		c. electric generators	a.	none
	a. 8	b. 3		c. 5	d.	7

48. When the potential difference of 4 volt is applied across resistance, 10J energy is converted. Find the charge flows.

a. 0.20 C

b. 2.5C

c. 5C

d. 10C

49. Electric power

a. V×I

b. W/t

c. V^2/I

 $d. E^2/t$

50. The fractional change in resistance per kelvin is known as,

a. temperature coefficient of resistance

b. coefficient of Voltage of charge

c. thermal expansion

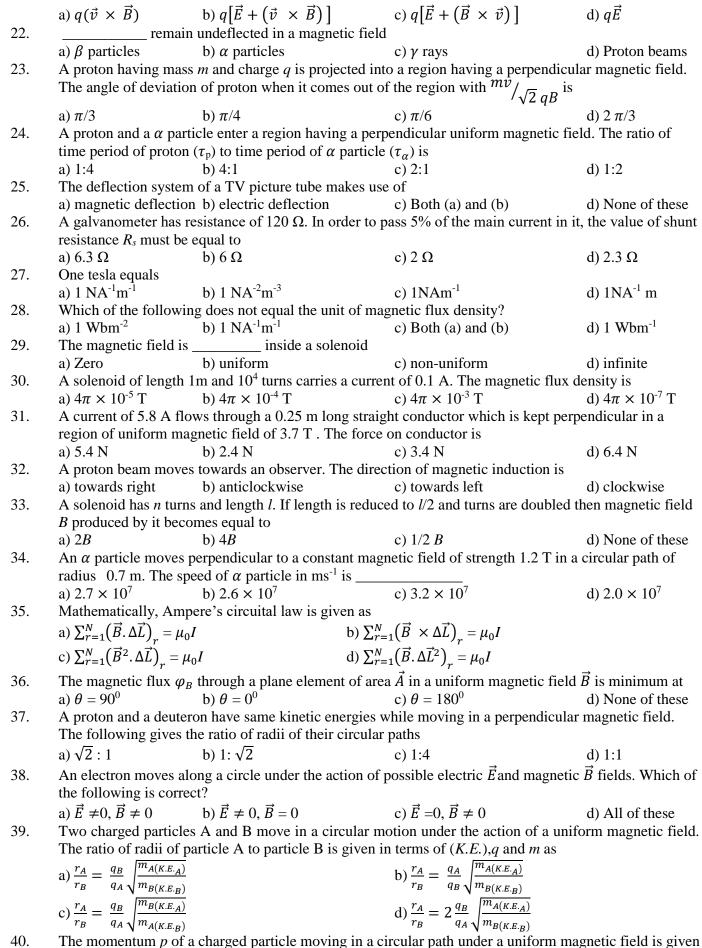
d. all of above

Answers key

1	A	11	A	21	В	31	С	41	C	
2	D	12	С	22	С	32	A	42	D	
3	A	13	A	23	В	33	A	43	В	
4	A	14	D	24	A	34	В	44	В	
5	A	15	С	25	С	35	D	45	В	
6	В	16	С	26	A	36	С	46	В	
7	В	17	C	27	A	37	В	47	C	
8	D	18	A	28	С	38	С	48	В	
9	A	19	В	29	A	39	D	49	A	
10	A	20	A	30	D	40	C	50	A	

CHAPTER 14

1.	An electron and a new acceleration is	utron enter a magnetic field wi	th the same velocity. Ratio of e	lectron to neutron's
	a) $\frac{m_n}{m_e}$	b) $\sqrt{\frac{m_n}{m_e}}$	c) $\sqrt{\frac{m_e}{m_n}}$	d) $\frac{m_e}{m_n}$
2.		=	e nature of force between them	
	a) Attractive		pendent on magnitude of velocit	•
3.		nagnetic field acting vertically d	lownwards with a velocity v fror	n west. The electron
	is deflected along			
	a) North	b) South	c) Northeast	d) Southeast
4.	A proton moves in a doubled then the new		ircular path of radius R. If the	energy of proton is
	a) $\frac{R}{\sqrt{2}}$	b) 2 <i>R</i>	c) $\frac{R}{2}$	d) $\sqrt{2} R$
5.		ffected by a magnetic field	´ 2	, ,
<i>J</i> .	a) Change in magnetic		h) a maying alastron	
	, ,		b) a moving electron	ator
6	c) a stationary proton		d) current flowing in a conduction	
6.			oton moves at right angles to a m	•
7	a) Momentum		c) Speed	d) All of these
7.		of a is achieved by	connecting a high resistance	R _h in series with a
	galvanometer	1) 01		
		b) Ohmmeter	c) LED	d) Voltmeter
8.		AVO meter is known as		
	a) Digital Ohmmeter		c) Digital Multimeter	d) None of these
9.	Sensitivity of a galvar	nometer can be increased by		
	a) Increasing the num	ber of turns of the coil	b) Decreasing the magnetic fie	eld
	c) Increasing the ratio	$\frac{c}{RAN}$	d) Decreasing the area of the	coil
10.			est is called a galvano	meter
	a) Ballistic	b) Mirror	c) Astatic	d) Dead beat
11.	Shunt resistance R_s is	,	,	,
			$_{\rm O}$) I $^{\rm D}$	d) None of these
	a) $\frac{I_g}{I-I_g} R_g$	b) $\frac{I_g}{I+I_g} R_g$	$C_{I-I_{g}}^{R_{g}}$	u) None of these
12.	A multipurpose instru	ment for measuring current, po	tential difference and resistance	is
	a) Ohmmeter	b) Astatic galvanometer	c) Rheostat	d) AVO Meter
13.	The of		of the spot formed on the screen	
	a) Filament	b) Grid	c) Deflection plates	d) Cathode
14.			al deflection plates is known as	,
	a) Time base generate	-	c) Thermionic diode	d) Zener diode
15.		is easier to use because	,	,
	a) It provides precise		b) It serves as a signal synchro	onizer
	c) It gives reading of		d) It eliminates human error d	
16.		_	galvanometer are made concave	
10.	a) decrease the streng		b) create a non-uniform magn	
	c) make the magnetic	•	d) All of these	ctic iicia
17.			deflection with 4 mA current. In	n order to convert it
17.		ge of 10 A is connected with it,		i order to convert it
	a) 0.1Ω	b) 0.2Ω	c) 0.06Ω	d) 0.03 Ω
10		,	,	
18.			the direction of a uniform magn	icuc neiu di U.8
	Tesla. The force on e		a) 4 N	d) 70rs
10	a) 8 N	b) 2 N	c) 4 N	d) Zero
19.	-	ced in a non-uniform magnetic	<u> </u>	1) NI
20	a) force and torque	b) only torque	c) only force	d) None of these
20.	•		charged particle in a circular par	
	a) $qvB \sin \theta$	b) $mg \sin \theta$	c) zero	d) $mg \cos \theta$
21.	The correct equation i	for Lorentz force is given as		



40. The momentum p of a charged particle moving in a circular path under a uniform magnetic field is given in terms of its kinetic energy and mass as

	a) $p = \sqrt{2(K.E.)m}$	b) $p =$	$\sqrt{(K.E.)m}$	c) $p = \frac{1}{2} \sqrt{(K.E.)m}$	d) None of these
41.	When a uniform magnetic fiel	dB is ap	plied to a curre	ent carrying coil, the coil will ro	tate in such a
	manner that its plane		•	•	
	a) becomes parallel to B			b) becomes anti-parallel to <i>B</i>	
	c) makes an angle of 60^0 with	B		d) becomes perpendicular to E	3
42.	The galvanometer used in sch	ool and c	ollege laborato	ories is a galvanom	eter.
	a) pivoted type	b) astat	ic	c) mirror	d) none of these
43.				s related to the angle of deflection	
	a) $I \propto \theta$				d) $I 1/\propto \theta^2$
44.	The high resistance R_h connection				
	a) $R_h = V/I_g - R_g$	b) $R_h =$	$= V/I_a + R_g$	c) $R_h = VI_g - R_g$	d) None of these
45.	The output waveform produce	ed due to	time base gene	erator in a CRO is	
	a) saw tooth		soidal	c) linear	d) helical
46.	The ratio of electric force F _E t	o magne	tic force F _B for	a moving charge is	
	a) E^2/vB	b) E/v_l	3	c) $B/_{vE}$	d) E/B
47.	The expression $\vec{F} = q\vec{E} + q(\vec{r})$	$\vec{v} \times \vec{B}$) re	presents	force	
	a) Maxwell		ritational		d) Lorentz
48.	The following expression give			, .	,
			$/_{B^2r^2}$		d) $Br/_{2V}$
49.	The anodes in a CRO are at _	,	notential w	ith respect to the cathode	, , ZV
.,.	a) negative	b) high	negative	c) high positive	d) positive
50.				up to 5 mA. If it is to read 100	
	resistance to be used in series			1	, 2
	a) 19998 Ω		5.8 Ω	c) 19995.5 Ω	d) 19996.5 Ω
			T 7		

Answer Key:

1.A	2.B	3.B	4.D	5.C	6.A	7.D	8.C	9.A	10.D
11.A	12.D	13.B	14.A	15.D	16.C	17.D	18.D	19.A	20.C
21.B	22.C	23.B	24.D	25.A	26.A	27.A	28.D	29.B	30.B
31.A	32.B	33.A	34.D	35.A	36.A	37.B	38.C	39.A	40.A
41.D	42.A	43.A	44.A	45.A	46.B	47.D	48.A	49.C	50.C

1.	The induced emf is p	roduced in a cir	rcuit due to:		
	a. Initial magnetic flu	IX	b. final magne	etic flux	
	c. Change of magneti	c flux	d. constant ma	agnetic flux	
2.	The Principle of an a	lternating curre	nt generator is	based on:	
				c. Faraday's law	d. Lenz's law
3.	If velocity of a condu	ctor moving th	rough a magne	tic field 'B' is made ze	ero, then
	Motional emf will be		<i>c c</i>		,
	a. –VBL	bV/BL		c. – BL/V	d. zero
4.	The current flowing i		induced emf de		
	_	b. resistance of		c. area of coil	d. magnetic flux
5.	Lenz's law is in acco				d. magnetic max
<i>J</i> .	a. momentum		omentum		d. energy
6.		_		ic field. The induced e	•
0.					
7				c. depends on nature	of loop a. zero
7.	The mutual inductance	ce of the con de			
	a. density of the coil		b. stiffness of		
0	c. material of coil	1	d. geometry o		.1 '1', 10' 11 1
8.					the coil itself is called:
0	a. mutual induction			c. self-inductance	d. mutual inductance
9.	The self-inductance of				
	a. $L = \mu nA/l$	•		c. $L = \mu n^2 A l$	d. $L = \mu n l/A$
10.	The energy density o	f an inductor is	•	2	2
	a. $B^2/2 \mu^2$	•		c. B/2 μ^2	d. $B^2/2 \mu$
11.				gy into electrical energy	
	a. mechanical energy	b. chemical en	nergy	c. solar energy	d. potential energy
12.	Eddy currents produc	ed in the core	of transformer a	are responsible for:	
	a. heat loss	b. Step up pro	ocess	c. Step down process	d. induction phenomena
13.	One henry is equal to):			_
	a. Vs ⁻¹ A	b. NmA ⁻¹		c. V ⁻¹ s A	d. V s A ⁻¹
14.	To construct a step de	own transforme	er, the condition	n is:	
				c. $N_p = N_s$	d. N_p . $N_s = 1$
15.				lied to its primary coil	
	secondary coil will b		· · ·	<i>y</i>	, , , , , , , , , , , , , , , , , , , ,
	a. 44V	b. 4.4 V		c. 220V	d. 1100V
16.			always so as to	o oppose the change w	
10.	Current" is the state		arways so as te	oppose the change wi	men eauses me
	a. Faraday's law	b. Lenz's Law	7	c. Ohm's Law	d. Kirchoff's rule.
17.	Electric current prod				d. Kirchoff's fulc.
1/.	a. Faraday	b. Lenz	neid was sugge	c. Ohm	d. Oerested
10	•		magnitude of '		d. Geresied
18.	If the motor is overlo		magnitude of		d Danamas zana
10	a. Increases	b. Decreases	DI -1 41	c. Constant	d. Becomes zero
19.		expression $\varepsilon = -$	VBL snows tha	t the angle between the	e direction of L and
	$(v \times B)$ is:	1 100		4.5	1.0
• •	a. 90	b. 180		c. 45	d. 0
20.	When a motor is just		mf is almost		
	a. Infinite	b. zero		c. minimum	d. maximum
21.	Farad is defined as:				
	a. Coulomb / volt	b. Ampere / v	olt	c. Coulomb / joule	d. Joule / Coulomb
22.	A transformer:				
	a. Works on A.C. onl	y	b. Works on I	O.C only	
	c. Works on A.C. and	l D.C	d. Has no hys	teresis loss	

23.	If magnetic field is do		gnetic energy d	•		
	a. Four times	b. Two times		c. Three times	(d. Six times
24.	A magnetic field acts a. speed	on a charged pa b. energy	articles so as to	o change its: c. direction of	motion (d all of these
25.	An ideal transformer a	<i></i>	ne law of conse			a. an or mose
20.	a. energy	b. momentum		c. charge		d. Flux
26.	The unit of inductance			e. charge		 110/1
20.	a. Volt			a Hanny		d. Ohm
27.	The application of mu	b. Ampere	ia•	c. Henry	•	u. Ollili
21.	a. TV	b. Radio	15.	c. Transforme	r	d. Motor
28.	The work is stored in		form of		L '	u. Motor
20.	a. Elastic potential end			etic energy		
	c. Potential energy	C16 y		nal potential en	erov	
29.	One henry is equal to		d. Glavitation	nai potentiai en	16)	
27.	a. VA/s	b. Nm/A		c. As/V		d. Vs/A
30.	Due to self-inductance		es are known as			
		b. Conductor		c. Inductor		d. Semi-conductor
31.	Energy stored per unit		the solenoid is			
	a. Energy density		b. Charge Der			
	c. Mass density		d. Volume ch	•		
32.	In the plane of the A.C	C generator coil		•	then indi	uced emf in
	the coil is:		1 1	•		
	a. Maximum	b. minimum		c. zero		d. intermediate value
33.	The loss of energy over	er each A.C cyc	cle magnetizati	ion and demagn	etization	of
	transformer, is called					
	a. Magnetization loss		b. Hysteresis	loss		
	c. Demagnetization lo	SS	d. energy loss			
34.	The principle of AC g	generator is:				
	a. Mutual induction		b. self induction	on		
	c. electromagnetic ind		d. Induction			
35.	A transformer steps de turns will be:	own 220V to 40	0 volts. If the s	econdary turns	are 40 th	nen primary
		b. 40		c. 120		d. 220
36.	The Si unit of mutual		l calf inductanc			u. 220
50.	a.same	b. different	i sen muuctanc	c. no unit	,	d. a & b
37.	The most common so		tage is:	c. no unit	,	a. a & o
37.	a. motor	b. generator	iage is.	c. cell	d. transf	former
38.	In motor a permanent	_	es:	C. CC11	G. Clarist	
	a. Electric field	b. electric flux		c. magnetic fie	eld	d. gravitational field
39.	Which one is not pres					<i>6</i>
	a. Armature	b. magnet		c. slip ring		d. commutator
40.	The induced current in	C	which produced			
	is known as:		1		1 1	,
	a. Conventional curren	nt	b. elec	ctronic current		
	c. Perpendicular curre	ent	d. Edd	ly current		
41.	In the plane of AC gen	nerator coil is p	parallel to the fi	ield, then emf in	nduced in	n coil is:
	a. maximum	b. minimum		c. zero	(d. intermediate
42.	Which component is a	mainly used in	a DC generator	r:		
	a.slip ring	b. commutate	or	c. magnet	(d. coil
43.	The phenomena of inc		observed by Fa	araday and Hen	ry in:	
	a. 1931	b. 1831		c. 1535	(d. 1940
44.	The induced current c		•			
	a. Using strong magne	etic field	b. moving loo	p faster		

c. Replacing loop by coil d. all of above Which of the following will produce an induced emf: 45. a. Changing area of coil b. Changing magnetic flux c. changing orientation of coil d. all of them 46. The induced emf in a coil depends upon: a. Strength of magnetic field b. Resistance of the coil c. area of the coil d. All of them Which of the following converts electric energy into mechanical energy: 47. b. DC generator d. AC generator a. Transformer c. Motor The only difference between construction of DC generator and Ac generator is that of: 48. a. carbon brush b. Bar magnet c. electromagnet d. Horseshoe magnet 49. Magnetic flux linked with a coil can be changed by using an: a. Permanent magnet b.Bar magnet c. Electromagnet d. Horseshoe magnet

Answers Key

c. Electric coil

d. simple coil

The windings of the electromagnetic are usually called:

b. Field coil

50.

a. Magnetic coils

1	c	11	a	21	a	31	a	41	a
2	c	12	a	22	a	32	c	42	b
3	d	13	d	23	a	33	b	43	b
4	b	14	b	24	С	34	С	44	d
5	d	15	d	25	a	35	d	45	d
6	d	16	b	26	c	36	a	46	d
7	d	17	d	27	c	37	b	47	c
8	b	18	b	28	c	38	С	48	b
9	c	19	b	29	d	39	d	49	c
10	d	20	b	30	c	40	d	50	b

1:	Al high frequency, the	he value of reactance of	of a capacitor in AC circuit will	be
	(a) Large	(b) Infinite	(c) Zero	(d) Small
2:	Al higher frequency	of the alternating curr	ent, the capacitive reactance 'Xa	· ·
	(a) Decreases	(b) ir	ncreases	
	(c) Remains the sam	e (d) se	ometime increases and sometime	es decreases
3:	In an inductive AC of	circuit, the current		
	(a) Leads the voltage	e by $90^{\circ} \pi/2$)	(b) Lag behind the voltage by	$790^{\circ} (\text{or } \pi/2)$
	(c) Lags behind the	voltage 180° (or π)	(d) Leas the voltage 1800 (or	π)
4:	The inductive reacta	nce 'XL' of coil of ind	uctance 'L' across and AC sour	ce is given by
	(a) $X_L=2\pi fL$	(b) $X_L = 2\pi f/L$	(c) $X_L=1/2\pi fL$	(d) $x_L = \frac{1}{\sqrt{2\pi f L}}$
5:	The indicative reacta	ance $'X_L'$ of inductor a	across an AC source is given by	
	(a) ωc	(b) ωL	(c) $1/\omega L$	(d) $\sqrt{\omega L}$
6:	The inductance and	capacitance behave as	a function of	` '
	(a) voltage	(b) current	(c) power	(d) Frequency
7:	` '	• •	an AC source is given by	· · · · · · · · · · · · · · · · · · ·
	(a) $2\pi f L$	(b) ωL	(c) V/I	(d) All of the above
8:	• •	nce of a coil is directly	` '	(.,
	(a) resistance		apacitance	
	(c) Inductance	` '	oth frequency of Ac and inducta	nnce
9:	` /	stance in AC circuit is		
	(a) current	(b) voltage	(c) power	(d) Frequency
10:	` /		the inductive reactance 'X _L '	(") 1
10.	(a) Zero	(b) Increases	(c) Decreases	(d) remains the same
11:	` /	the alternating curren	` '	(a) remains the same
11.	(a) Small	(b) large	(c) Zero	(d) infinite
12:	` '	reactance of a coil are	(6) 2618	(4) 11111111
12.	(a) Henry	(b) Hertz	(c) Ampere	(d) Ohms
13:	Power dissipated in	` '	(e) / impere	(d) Ollins
13.	(a) Large	(b) Small	(c) Infinite	(d) Zero
14:		oil changes directly wi		(d) Zero
1	(a) The inductance	on enanges affectly wi	(b) Frequency of AC	
	` '	and frequency of AC	(d) capacitance	
15:			etance in AC circuit is called	
15.	(a) Conductance	(b) Impedance	(c) Resistance	(d) choke
16:	` '	· · ·	voltage to the rms value of resul	· ,
10.	(a) Reactance	(b) resistance	(c) impedance	(d) conductance's
17:	SI unit of impedance	` '	(c) impedance	(u) conductance s
1/.	(a) henry	(b) Hertz	(c) ampere	(d) ohms
18:	Ohms is the unit of	(b) Hertz	(c) ampere	(u) omins
10.	(a) resistance	(b) reactance	(c) impedance	(d) all of the above
19:	• *	ated in AC circuit is gi	` ' •	(u) all of the above
17.	(a) $P=I^2Z$	(b) P=VISinθ	(c) P=I ² XL	(d) P=VI Cosθ
20:	` '	$V \cos\theta$, $\cos\theta$ is called	(C) F=1 AL	(u) r - v1 C080
20.	(a) phase angle	(b) limiting angle	(a) Critical angle	(d) nower angle
21:	· / I		(c) Critical angle	(d) power angle
21.	• •	-	or capacitance circuit is	(d) Madamata
22.	(a) Zero	(b) Maximum	(c) Minimum	(d) Moderate
22:			ge are in phase, the power factor	
22.	(a) One	(b) Zero	(c) infinity	(d) 0.5
23:		t, the true condition of		(d) V -> V
	(a) $X_L > X_c$	(b) $X_L < X_c$	(c) $X_L = X_c$	(d) $X_C > X_L$

24:	A resonance curve for	r RLC series circuit is a plot of	of frequency versus	
	(a) voltage	(b) resistance	(c) current	(d) impedance
25:	At resonance frequen	cy, the impedance of RLC ser	ries circuit is	· · · · · · · ·
	(a) zero	(b) minimum	(c) maximum	(d) moderate
26:	The impedance of RL	C series circuit resonance circ	cuit at resonant frequen	acy is
	(a) Less than R	(b) Greater than R	(c) Equal to R	
		r and sometime greeter than F		
27:	In RLC series circuit,	the current at resonance frequency	uency is	
	(a) Minimum	(b) Zero	(c) maximum	(d) infinite
28:	The total reactance of	a series RLC circuit at resona	ance is	
	(a) Equal to the resist	* *	(c) infinity	(d) 1
29:	If the value of C in a	series RLC circuit is increased		
	(a) increases	(b) Decrease		(d) Becomes infinite
30:	St resonance frequence	cy, the impedance of L-C para		
	(a) Zero	(b) Infinite	(c) Minimum	(d) Maximum
31:		circuit, the capacitor draws a		
		(b) Lagging current	(c) Leading current	(d) Zero current
32:	In L-C parallel circuit			
	(a) Leading Current		(c) Main current	(d) zero current
33:	-	arallel circuit produces resona	•	
	(a) $X_L > X_C$	• •	(c) $X_L = X_C$	(d) R = 0
34:		series RLC at resonant freque		
	(a) 90°	(b) 0°	(c) 180°	(d) -90°
35:		ant circuit, the value of resista		
	(a) LCR	(b) L/CR	(c) L/CR ²	(d) L/C^2R
36:		onant circuits, the current at re		(1)
. –	(a) Maximum	(b) Minimum	(c) infinite	(d) Zero
37:		In L-C parallel resonant circu		(1) 10
20	(a) 100	(b) zero	(c) 1	(d) 10
38:		t of frequency 1000 kHZ with	a inductor of 5mH, the	e capacitance will be
	required	(1) 0 F	() 2 F	(1) 5 00 E
20	(a) 10pF	(b) 8pF	(c) 3pF	(d) 5.09pF
39:	A three phase AC ger		() (1 '1	(1) E '1
40.	(a) one coil	(b) Two coil	(c) three coil	(d) Four coil
40:		generator the phase difference	-	<u>=</u>
41.	(a) 45°	(b) 90°	(c) 120°	(d) 180°
41:		generator, if the first coil has p		(d) 20° and 160°
42.	(a) 20° and 140°	(b) 120° and 240	(c) 120° and 160°	(a) 20° and 100°
42:		C supply can be divided into	(a) 1 manta	(4)
12.	(a) 2 parts Metal detectors can b	(b) 3 parts	(c) 4 parts	(d) many parts
43:			atal ahiaat	
	(a) buried metal objects(c)flying meta objects	· · · ·	of buried object	
44:	A chock coil is used a	1 /	or buried object	
44.	(a) AC circuit	(b) potential divider	(c) DC current	(d) Wheatstone bridge
45:	Chock consumes extr	· · ·	(c) De current	(u) wheatstone bridge
45.	(a) charge	(b) current	(c) power	(d) potential
46:	` '	not require any material medi	· / •	` ' =
- 0.	(a) mechanical waves	- · · · · · · · · · · · · · · · · · · ·	tionary waves (d) ele	
47:		vere discovered by James Cla	• • • • • • • • • • • • • • • • • • • •	enomagnene wavers
т/.	(a) 1870	(b) 1970	(c) 1864	(d) 1831
48:	A changing electric fl	` '	(0) 1001	(4) 1001
	(a) electric field	(b) magnetic filed	(c) electromagnetic fi	led (d) None
	· /	· / · · · · · · · · · · · · · · · · · ·	()	(/

- 49: A changing magnetic field creates an
 - (a) magnetic field
- (b) electromagnetic filed
- (c) electrostatic field (d) electric filed
- 50: The most common source of AC voltages is
 - (a) motor
- (b) cell

- (c) AC generator
- (d) Ac transformer

Answers Key

1d	11a	21d	31c	41b
2a	12d	22a	32b	42b
3a	13d	23c	33c	43a
4a	14c	24c	34b	44d
5a	15c	25b	35b	45c
6d	16c	26c	36b	46d
7d	17c	27c	37c	47d
8d	18a	28b	38d	48b
9d	19a	29b	39c	49b
10c	20d	30d	40c	50c

1.	An element which has a defi	inite volu	me and shape is calle	d:			
	a) Liquid	b) Solie	d	c) Gas		d) Var	oour
2.	A solid is which atoms are in	n a regula	ar order is called				
	a) Crystalline solid		orphous solid	c) Poly	meric solid	d) Gla	ssy solid
3.	Which of the following is a contract the following is a co	crystallin	e solid?				-
	a) Copper	b) NaC	1	c) Zirc	onia	d) All	of above
4.	Which of the following is po	olymeric	solid?				
	a) Nylon			c) Poly	thene	d) All	of above
5.	Molecules of a solid possess	,		, ,		,	
	a) Rotational motion			b) Vib	rational motion	l	
	c) Translational motion			d)	All of above		
6.	A solid in which there is no	regular a	rrangement of molecu	,			
	a) Amorphous	b) Crys	_	c) Cop	per	d) Noi	ne of above
7.	Which class of material wou			· / - · I	r -	/	
	a) Fibres	b) Poly		c) Cera	amics	d) Gla	SS
8.	The deformation of body is the	,		0) 001		<i>a</i>) 014	
·.	a) Shape	b) Leng		c) Area	a	d) All	of above
9.	A smallest three dimensional			,	•	<i>a)</i> 1 III	01 400 10
·	a) A particle		olecules	c) A u	nit cell	d) An	atom
10.	The pattern of NaCl particles		orceares	C) 11 ui	nt cen	u) / III	atom
10.	a) Triangular		a r o	c) Cub	ic	d) Re	ctangular
11.	When stress changes the sha	, .		c) Cub	ic	u) Re	ctangulai
11.	a) Shear stress			nnreccis	e stress d)vol	umetric	ctrace
12.	The unit Nm ⁻² is also called		sile siless () Col	прісвы	c suess 'd)voi	umeme	, sucss
12.	a) Coulomb	b) New	ton	c) Pas	oo1	d) Am	noro
13.	Stress is defined as:	U) NEW	ton	C) Fas	cai	d) Am	pere
13.		1-)	E/A2	2)	A /IE	٦١/	Ε Λ
1.4	a) F/A	b)	F/A^2	c)	A/F	d)	FxA
14.	S.I unit of stress is:	1 \ > 7		\ N T -	-2	1\	
1.5	a) N/m	b) N m		c) Nm	_	d) Nev	wton
15.	The ability of a body to return				G	1\	G .
	a) Plasticity		Elasticity	c)	Strain	d)	Stress
16.	The strain due to tensile stre						
	a) Compressive strain	b) Shea	ar strain	c) Vol	umetric strain	d) Ten	isile strain
17.	S.I unit of strain is		2				
	a) Newton	b) N m		c)	Pascal	d) no ı	unit
18.	When stress changes the length	_	=				
	a) Tensile stress	b) Shea		c) Con	npressive stress	d) Yie	ld stress
19.	The deformation of a solid w						
	a) Strain	b) Elas	ticity	c)	Rigidity	d) Pre	ssure
20.	The S.I Unit of Modulus elas	-					
	a) Pascal	b)	Coulomb	c) Am	pere	d) Nor	ne
21.	The volumetric strain is:						
	a) $\Delta V/V_o$	b) V_o/Δ	۸V	c) $\Delta V/$	t	d) Nor	ne
22.	The ratio of stress to strain i:	:					
	a) Modulus of conducti	ivity	b) Modules of	f Elastic	ity		
	c) Modulus of electricit	ty	d) Modulus o	f Viscos	ity		
23.	Young's Modulus is given b	•	•				
	a) $(F/A) / (\Delta V/V)$	•	$(F/A) / (\frac{\Delta \ell}{\ell})$	c) (FA) / $(\frac{\Delta \ell}{\rho})$	d) (F/A	Α) / (ΔV)
24			~		ℓ		
24.	The ratio of shear stress to sl			D.,11- 1	Modulya	d)M	a of obarra
	a) Shear modulus	o) i our	ng's Modulus c)	DUIK N	TOUUIUS	ujiyon	e of above

25.	The ratio of stress to volume			
		b) Young's Modulus c) Bul	lk Modulus d) Mo	odulus of elasticity
26.	The dimension of strain is	2 2	1 2	
	a) [L]	b) $[ML^2T^{-2}]$	c) $[M L^{-1} T^{-2}]$	d) Dimensionless
27.	The substance which break j			
	a) Ductile	b) Brittle	c) Soft	d) Hard
28.		o plastic deformation until bre		
	a) Brittle	b) Ductile	c) Hard	,
29.	When stress is increased bey	ond elastic limit and material		
	a) Permanent stress	b) Elasticity	c) Yield strengt	h d) Plasticity
30.	The maximum stress that a b			
	a) UTS	•	c) Elastic strength	d) Plastic stress
31.	The strain energy in a deform	med material is:		
	$1(E\ell_1)$	$1 \left(EA\ell_1 \right)$	$1(EA\ell_1^2)$	$1(-\ell_1)$
	a) $\frac{1}{2} \left(\frac{E\ell_1}{AL} \right)$	b) $\frac{1}{2} \left(\frac{1}{L} \right)$	c) $\frac{1}{2} \left(\frac{EA\ell_1^2}{L} \right)$	a) $\frac{1}{2} \left(E \frac{1}{L} \right)$
22				2(L)
32.		ity of the order of $10^{-6} - 10^{-4}$ (1 1 .
22		b) Super conductors c) Sen		od conductors
33.	•	petween $10^{-10} - 10^{-20} (\text{n m})^{-1}$		1 1 .
2.4	a) Insulators b)	, I	er conductors d)Goo	od conductors
34.	Good conductors have condu	•	107(0)-1	1) 10-9 (0)-1
25	a) $10^{-10} (\Omega \text{m})^{-1}$		c) $10^{7} (\Omega \text{m})^{-1}$	d) 10 × (22m) 1
35.	The electrons in the outermo		\m'' 1 \d 1 1 1	1) (0) (1)
26	a) Valance electrons	*	c) Tightly bound	d) Stationary
36.	The band above the valance		\T 1'11 1 1	1\ ' 11 1
27	a) Conduction band	*	c) Forbidden band	d) occupied band
37.	<u> </u>	npurity in pure semiconductor		J) To and Add a
20	a) Doping	b) Radiating	c) Mixing	d) Insulating
38.		addition of trivalent impurity		d) M. Tyma
39.	a) P–TypePure semiconductors silicon	* * *	c) Q-type	d) M–Type
39.	a) Extrinsic	_	c) Insulator	d) Diodes
40.	A doped semiconductor is ca	*	C) Ilisulatoi	d) Diodes
40.	a) Extrinsic b) Intr		ulator d) Co	nductor
41.	Conductivity of semi conduc	·	urator u Co	inductor
41.	a) Decrease of temperat	•	rature constant	
	c) Increase of temperatu			
42.	A combination of N-type and			
12.	a) Diode	b) Transistor	c) Resistor	d) Capacitor
43.	In a P-type semiconductor th	,	c) resistor	a) capacitor
	a) Electrons	b) Holes	c) Protons	d) Neutrons
44.	In the N-type semiconductor	,	c) 11000110	a) 1 (5 a) 2
	a) Holes	b) Neutrons	c) Protons	d) Electrons
45.	The majority carriers in N-ty	,	-,	.,
	a) Holes	b) Protons	c) Neutrons	d) Electrons
46.	Minority carriers in N-type a	,	,	,
	a) Holes	b) Electrons	c) Neutrons	d) Protons
47.	,	aterial show super conductivity	· ·	,
	a) Super temperature	b) Critical temperature	c)Kelvin temperature	d)Absolute
	temperature	-, temperature	-, temperature	<i>2</i> ,1 20001440
48.	First super conductor was di	scovered by		
	a) Kelvin	b) Hertz	c)Einstein d) Ka	amerlingh Ornes
49.	The most suitable metal for	making permanent magnet is		-

	a) I	ron	b) Ste	eel	c)	Silver	d) Copper
b)	The	energy required to ma	ignetize and	demagnetize is called			
	a)	Saturation	b)	Retentivity	c)	Coercivity	d)
	Hyst	teresis loss					

Answer Key

1	В	11	A	21	A	31	C	41	D
2	A	12	C	22	В	32	D	42	A
3	D	13	A	23	A	33	A	43	В
4	D	14	C	24	В	34	C	44	D
5	В	15	В	25	C	35	A	45	D
6	A	16	D	26	D	36	A	46	A
7	В	17	D	27	D	37	A	47	В
8	D	18	A	28	D	38	A	48	D
9	C	19	A	29	D	39	В	49	A
10	C	20	A	30	A	40	В	50	D

2. The process of conversion of AC into DC is called (a) Amplification (b) rectification 3. Which is the most important building block of electronic dev (a) Diode (b) p-n junction 4. N-type region has majority charge carriers as (a) Holes (b) protons 5. Photo diode operates in the condition (a) Forward bias (b) null 6. The potential barrier for germanium is (a) 0.6 V (b) 0.2 V 7. In transistor, the base region is of the order of (a) 10 ⁻⁵ m (b) 10 ⁻² m 8. In n-p-n transistor, p works as (a) Collector (b) emitter 9. The electronic circuits which implement the various logic op (a) Logic gates (b) Boolean algebra functions 10. Depletion region carries (a) +ve charge (b) -ve charge 11. Process of conversion low voltage to high voltage is called (a) Rectification (b) forward bias 12. The open loop gain of the amplifier is (a) 10 ⁵ (b) 10 ³ 13. Semiconductor germanium and silicon are (a) Pentavalent (b) trivalent 14. In p-n-p transistor, collector current is (a) Equal to emitter current (d) and 15. The operation of a transistor requires (a) Emitter is heated (b) base is heated (c) collector Non-inverting amplifier circuits have (a) Very high input impedance (b) ver	(c) purification vices? (c) transistor (c) neutrons (c) both a & d (c) 0.3 V (c) 10 ⁻⁸ m (c) base perations are called (c) amplifier gain (c) no charge	(d) rectifier (d) electrons (d) reverse bias (d) 0.5 V (d) 10 ⁻⁶ m (d) any of above (d) logic (d) all of above (d) amplification (d) 10 ⁸ (d) tetravalent
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15. The operation of a transistor requires (a) Emitter is heated (b) base is heated (c) col 16. Non-inverting amplifier circuits have (a) Very high input impedance (b) very	ly of above	
(a) Emitter is heated (b) base is heated (c) col 16. Non-inverting amplifier circuits have (a) Very high input impedance (b) very		
16. Non-inverting amplifier circuits have (a) Very high input impedance (b) very		
(a) Very high input impedance (b) ver	lector be heated (d)	none of above
(c) low output impedance (d) not	ry low input impeda	nce
	ne of above	
17. In forward bias, the width of potential barrier		
(a) Increases (b) decreases	(c) remains same	(d) no effect
18. An OP-AMPs can amplify	,	` '
(a) D.C (b) A.C	(c) both A.C & D.O	C (d) none of above
19. For normal operation of a transistor, the collector base junct	• •	(4) 110110 01 4100 10
(a) Unbiased (b) forward biased	(c) reverse biased	(d) none
20. The potential difference set up across the depletion region is	` '	(d) Hone
	(c) reverse potentia	ol (d) notantial
(a) Absolute potential (b) neutral potential	(c) reverse potentia	al (d) potential
barrier		
21. The number of diodes used in bridge rectifier circuit is	() a	(1) -
(a) 4 (b) 3	(c) 2	(d) 5
22. SI unit of gain of amplifier is		
(a) Volt (b) ampere		(d) dimensionless
23. P-n junction when reversed biased acts as a	(c) coulomb	(a) difficusionless
23. 1 - II junction when reversed blased acts as a	(c) coulomb	(a) difficusionless
(a) Capacitor (b) inductor	(c) coulomb(c) on switch	(d) off switch

	- · ·	(b) majority carriers	(c) hole	es	(d) electrons
25.	The operational amplifier is _				
	(a) High gain amplifier			power amplif	fier
	(c)high resistance amplifier		(d)low resistance	ce amplifier	
26.	In the transistor schematic syn	nbol, the arrow			
	(a) located on emitter		(b) located on b		
	(c) located on collector		(d) points from	north to south	1
27.	Depletion region of a junction				
		ring process	(b) under forwa		
	(c) under reverse bias		(d) when tempe	rature varies	
28.	A sensor which changes light				
		(b) thermistor	· · ·		(d) photovoltaic
29.	Devices which convert various				
	(a) Control system	(b) sensors	(c) level	sensors	(d) LDR
30.	A light emitting diode emits li				
		(b) forward biased		ased	(d) none
31.	The reverse current through se		lue to		
	(a) Minority carrier		(c) elec	trons	(d) holes
32.	The gain G of non-inverting as	mplifier is			
	(a) $G = -\frac{R2}{R1}$	(b) $G = 1 + \frac{R2}{R4}$	(c) G =	R2	(d) $G = 1 - \frac{R2}{R4}$
33.	The circuit which changes inp				R1
55.	<u> </u>	(b) operational ampli	-		(d) inverter
34.	Transistors are made from	(b) operational ampli	(c) switch	211	(a) inverter
<i>J</i> 1.		(b) metals (c)inst	ılators ((d) doned sem	iconductors
35.	The current gain β of transisto	• •	ilato15 ((a) doped sem	nconductors
33.	Ic Ic	IE IE	() 0	Ic	(I) O IB
	(a) $\beta = \frac{Ic}{IB}$	(b) $\beta = \frac{1}{Ic}$	(c) β =	IC IE	(a) $\beta = \frac{1E}{1E}$
36.	LDR is abbreviated as				
	(a) Light dependent resis	stance		depositing re	sistance
	(c) Light doped resistance		(d) all o	f these	
37.	A photodiode can switch its cu				
	(a) nano second		* *		(d) centi second
38.	Current gain of a transistor v	which has collector curi	ent of 10 mA an	d a base curre	ent of
	40 micro Ampere is:				
	(a) 25	(b) 250	(c) 2500		(d) 25000
39.	A part of transistor which is	• • •	_		
	(a) Emitter	(b) Base	(c) Colle	ector	(d) any of above
40.	The output of two inputs OR				
	(a) Both are one	(b) Both are zero	(c) Eithe	er input is 1	(d) None
41.	Silicon transistors are prefer				
	(a) High operating temperatu			v leakage curr	ent
	(c) Suited to high frequency		(d) All		
42.	The emitter of a transistor is	-			
	(a) Acts as a supplier of char	ge carriers		ipates maxim	-
	c) has a large resistance		` '	a small resista	
43.	In a semiconductor diode, p-	side is earthed and to r	-side is applied a	a potential of -	-2 volt; the diode
	shall				
		ot conduct	(c) Conduct par	• •	
44.	In a transistor, the convention				
	(a) NPN (b) Pl		(c) FET	(d) No	one of these
45.	If PN junction is forward bi				
	(a) Zero (b) Int		(c) A few ohm	, ,	ew kilo ohms
46.	In a half wave rectifier the r	ms value of AC compo	nent of the wave	es	

	(a) Zero		(b) Equal to DC value				
	(c) More than DC value		(d) Less than DC value				
47.	On increasing the reverse bia	s to a large valu	ue in a j	p-n junction diode cui	rent		
	(a) Increases slowly			(b) Remains fixed			
	(c) Suddenly increases			(d) Decreases slowly			
48.	In the reverse biased p-n jun	ction, the curre	nt is of	the order of			
	(a) Ampere	(b) Milliampe	ere	(c) Microampere	(d) Nano-ampere		
49.	The output from a full wave	rectifier is					
	(a) A pulsating uni-directional current		(b) A	DC voltage (c) Zero	(d) An AC voltage		
50. Under ideal conditions, the collector current is							
	(a) Equal to base current			(b) Nearly equal to	emitter current		
	(c) Less than base current			(d) always zero			

Answers Key

1	В	14	С	27	A	40	В
2	В	15	D	28	A	41	D
3	В	16	A	29	В	42	A
4	D	17	В	30	В	43	A
5	D	18	В	31	A	44	A
6	С	19	С	32	В	45	С
7	D	20	D	33	D	46	В
8	С	21	A	34	D	47	С
9	A	22	D	35	A	48	D
10	С	23	D	36	A	49	A
11	D	24	В	37	A	50	В
12	A	25	A	38	В		
13	D	26	A	39	A		

1.	Which one of the following	waves re	quires a materia	ıl mediı	am for their pro	opagation?		
	a) Light waves	b)	X– rays	c)	γ-rays	d)	Sound waves	
2.	Which one of the following so	cientists re	garded light as eld	ectroma	gnetic waves?			
	a) Newton	b)	Galileo	c)	de Broglie	d)	Maxwell	
3.	Tick the wrong statement.							
	a) Velocity of light is indep	endent of	the motion of the	he obse	rver.			
	b) Velocity of light in free s							
	c) Velocity of light in free s	-						
	d) Absolute motion or absolute	lute rest is	s meaningless to	talk ab	out			
4.	Which one of the following	physical	quantities is ind	lepende	ent of relativisti	ic speed?		
	a) Mass		Length	c)	Time	d)	Charge	
5.	Relativistic velocity is of th		_				C	
	1			1.	1	1 '4 (1' 1	,	
	a) $\frac{1}{15}$ of the velocity	of light		b)	$\frac{1}{20}$ of the ve	clocity of ligh	1t	
	c) $\frac{1}{10}$ of the velocity	of light		d) A	ll the above			
6.	With increase in the velocit		siect its mass wi	:11				
0.	a) Increase		ecrease c)		in constant	d) None of	f the above	
7.	The relativistic energy 'E' i	,	,			u) None o.	the above	
	The relativistic energy E						_2	
	a) Ec^2	b)	$\frac{E}{c^2}$	c)	$\frac{E}{}$	d)	$\frac{c}{-}$	
8.	The length of rod at rest as	s measure	ed by an observe	er movi	ing parallel to	it with relat	ivistic speed is	
	given by,							
	a) $\ell = \ell_0 \left(1 - \frac{v^2}{c^2} \right)$	1-11 1	$\sqrt{v^2}$	2) ($\ell_{ {\sf o}}$	<i>a</i> \ 1 1	$\sqrt{v^2}$	
	a) $\ell = \ell_0 \left(1 - \frac{1}{C^2} \right)$	b)I I	$10 \sqrt{1-\frac{1}{c^2}}$	c) $\ell =$	=	a) $I_0 = I$	$\sqrt{1-\frac{c^2}{c^2}}$	
			, ,		$\sqrt{1-\frac{v}{2}}$, ,	
•		, ,			/ C-	•.		
9.	A rod at rest appears to an o		ust a mere point			-		
	a) Equal to the speed		1.	b)	Double the s			
10	c) Three-fourth the sp		ght	d) N	one of the above	ve		
10.	0.001 Kg mass will be equi		00 44 1) 0 24	5 - 1 44 1	4) N	2411	
11	a) 2.50 Giga watt hour		~ ~		~ ~	a) None of	the above	
11.	Which one of the following			_	•	1)		
10	a) T.V. waves	b)	Micro waves	c)	X-rays	a)	γ - rays	
12.	The electron was discovered	•	A 1	,	C_1 1 : 1	1)	I I TO	
12	a) Burcherer	b)	Anderson	c)	Chadwick	a)	J. J Thomson	
13.	The SI unit of Planck's con		I 1 - C 2	- \	T1- C	.1\	I1- C2	
1.4	a) Joule – Sec ⁻¹	b)	Joule – Sec ⁻²	c)	Joule – Sec	a)	Joule – Sec ²	
14.	Photoelectric effect was disco	•	D Thomas	2)	II alleva alea	ال.	Lamond	
15	a) Einstein	,	P.Thomson	c)	Hallwachs	· · · · · · · · · · · · · · · · · · ·	Lenard	
15.	If the distance of an electric	-	m a pnoto cell is	continu	lously increase	ea, the photo	electric current	
	(I) varies with distance (d) a				1		1	
	a) $I \propto d^2$	b)	$I \propto d$	c)	$I \propto \frac{1}{2}$	d)	$I \propto \frac{1}{d}$	
	,	•		,	d^2	,	d	
16.	Tick the wrong statement			C				
	a) No photoelectric e		-	_	•		-	
			a certain critical			-	У	
	b) Threshold frequen	cy depen	b) Threshold frequency depends upon the nature of the metal surface					

Photoelectric effect is an instantaneous phenomenon.

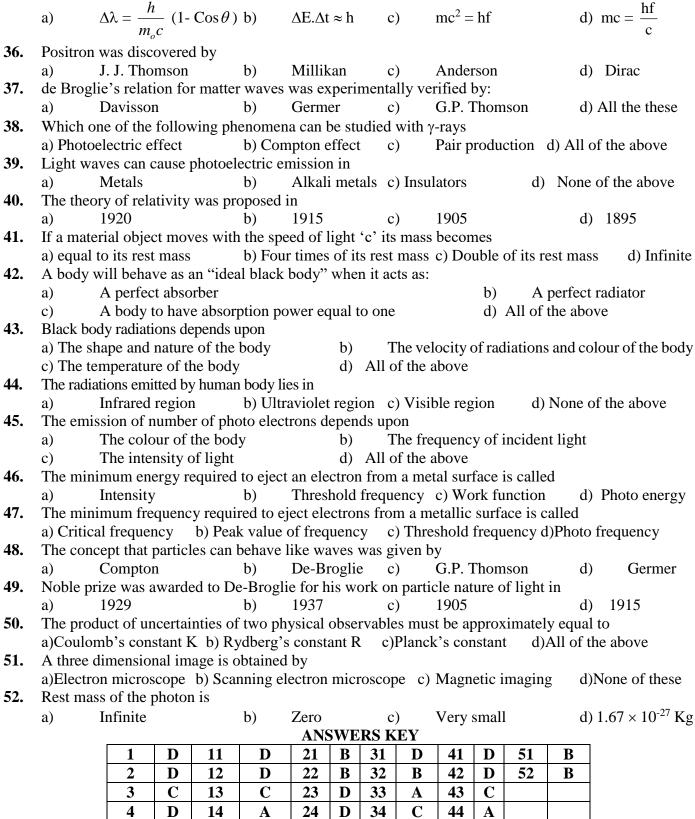
Maximum energy of a photoelectron is a function of intensity rather than frequency of

c)

d)

radiation

17.	Tick th	e correct statement						
	a)	Threshold frequency	is the g	reatest and thr	eshold v	wavelength is the sho	rtest.	
	b)	Threshold frequency	is the s	mallest and thi	reshold	wavelength is the gre	atest.	
	c)		ency and	wavelength are	neither	too large nor too small		
	d)	None of the above						
18.	The line	ear momentum of a ph	noton is					
	`	7	1 \	hf	`	hf	1)	$\frac{c^2}{hf}$
	a)	Zero	b)	$\frac{c}{c^2}$	c)	<u></u>	d)	$\frac{\overline{hf}}{hf}$
10	A davia	a basad on mbata alaa	tmia affa	ot is called		Ü		11)
19.		ce based on photo elec			a) Dh	ata ayınthasis	d) Dho	to 2011
20	a)	Photo sensitive			C) PII	oto synthesis	d) Pho	to cen
20.	A Com	pton shift in waveleng	ui is giv	en by		1		
	a) $\Delta \lambda =$	$= \frac{h}{m_0 c} (1 + Cos\theta) $ b)	$\Delta \lambda =$	$\frac{n}{2}(1+Cos)$	θ) c) Δ .	$\lambda = \frac{nc}{m} (1 - Cos\theta) d$	None of the	e above
	,	$m_{O}c$		$m_{o}c^{2}$, ,	m_o		
21.	Compto	on wavelength is giver	ı by					
	`	$\frac{h}{m_0c^2}$	1 \	h		hc	1)	$m_o h$
	a)	$\frac{1}{m_{\cdot}c^2}$	b)			$\frac{c}{m}$	a)	<u> </u>
22.		•		-				
44.	_	enomena of pair produ 10.2 MeV		1.02 MeV				
23.	a)		,			,		
23.		gy of incident photon is		r than the rest	mass en	lergy of electron posi	tron pair,	me surpius
	U 3	is shared by the pair a	*	The aure of a sec		a) Elastraria arrana	d) V:	·:
24	a)					c) Electronic energy	y a) Kine	nc energy
24.		one of the following q					J\ A11	ĺ
25	a)	Energy		Charge	C)	Linear momentum	a) All	L
25.		esence of anti-matter w	-		,	E' . '	1) (7)	1 1 '
26	a)	P.A.M Dirac	b)	Anderson			,	mberlain
26.		of the following pheno						
25	a)	Reflection	,	fraction	c) Pol	arization d) Interference	ence and d	iiiraction
27.		ncept of matter waves			-)	Din Main	-1\	
		sson and Germer	D)	de Brogne	c)	Einstein	d)	
20	Schrodi	•	. ,	1 24	1.			
28.	The wa	velength of the wave						and b
	a)	$\lambda = \frac{mv}{b}$	b)	$\lambda = \frac{h}{mv^2}$	c)	$\lambda = \frac{n}{n}$	d)	$\lambda = \frac{mh}{m}$
	,						,	V
29.		velength of the wave a			0 3	ect is		
	a)	Directly proportiona		_	_			
	b)	Directly proportiona		-	_	_		
	c)	Inversely proportion		•		ating voltage		
	d)	Inversely proportion		_	oltage			
30.		ainty principle was pre		•				
	a)	Dirac	,	Broglie	c)	Shrodinger	d) W. l	Heisenberg
31.	Pair pro	duction can be studied						
	a)	Ultraviolet rays		X-rays	c)	Microwaves	d)	γ-rays
32.	In the a	nnihilation of matter t	he numb	_	produce	d is		
	a)	One	b)	Two	c)	Three	d) No	ne
33.	In annil	nilation of matter the p		•		-		
	a)	Light	b) So		c) Tw	rice the speed of light	d) Non	e
34.	Tick the	e correct relation for u	ncertain	ty principle				
	a)	∆p ∆t ≈h	b)	$\Delta x \Delta t \approx h$	c) An	Λv ≈h	d) Δp	$\Delta \mathbf{x} \approx \frac{1}{-}$
	u <i>)</i>	⊿р ∆ι ~п	0)	ΔΛ Δι ~ II	с) Др	<i>△</i> Λ ~II	и) др	h
35.	Select t	he alternative from of	uncerta	inty principle f	rom the	following		



				ANS	SWE	RS K	EY				
1	D	11	D	21	В	31	D	41	D	51	В
2	D	12	D	22	В	32	В	42	D	52	В
3	C	13	C	23	D	33	A	43	C		
4	D	14	A	24	D	34	C	44	A		
5	D	15	C	25	A	35	В	45	C		
6	A	16	D	26	D	36	A	46	C		
7	В	17	В	27	В	37	D	47	C		
8	A	18	C	28	C	38	C	48	В		
9	A	19	D	29	C	39	A	49	A		
10	В	20	A	30	D	40	C	50	C		
					-						

1.	emitted or absorbed by atom		ion of wavelengths of e	lectro magnetic radiation
	•		a) radiogaany	d) staroosoony
2	a) spectroscopy		c) radioscopy	d) stereoscopy
2.	Black body radiation spectru	-	-\ 1!	1) -4
2	a) band spectra b) con		c) discrete spectra	a) atomic spectra
3.	Molecular spectra is an exan		\ 1	10
	a) continuous spectra		c) band spectra	d) atomic spectra
4.	Atomic Spectra is an example			
	a) discrete spectra	-	· -	· •
5.	In order to obtain spectrum			
	a) much less than atmospher	ic pressure	b) much high than atm	
	c) atmospheric pressure		d) high pressure and to	-
6.	Line spectrum is obtained or	the screen in the form	of lines if the slit in fro	ont of the source is
	a) narrow square	b) broad square	c) narrow rectangle	d) broad rectangle
7.	The fact that the spectrum of			
`	utilized in the second half of	thein identify	ring different elements.	
	a) 16 th century	b) 17 th century	c) 18 th century	d) 19 th century
8.	The first Hydrogen spectral s			
	a) J.R.Rydberg			d) F. S. Brackett
9.	The only series which lies in			
	a) Paschen series	_		
10.	The results obtained by the E	, ,	· · · · · · · · · · · · · · · · · · ·	.,
	a) Theodore Lyman			g d) LLBalmer
11.	The value of Rydberg's con		0) 01111111 0001	<i>b a</i> ,
11.	a) $1.0974 \times 10^{-7} \mathrm{m}^{-1}$	b) $1.0974 \times 10^7 \mathrm{m}^{-1}$	c) $1.0974 \times 10^7 \mathrm{m}^{-2}$	d) $1.0974 \times 10^{-7} \mathrm{m}^{-2}$
12.	The S.I. unit of Rydberg's c		c) 1.05/ / A 10 III	u) 1.05 / / A 10 III
12,	a) m ⁻²		c) cm ⁻¹	d) cm ⁻²
13.	The region where the Lyman	,	,	
13.	a) visible region			d) none of these
14.	Three spectral series, pasche			
14.	a) ultraviolet region			
15.				
13.	For Hydrogen atom, the allo		te those whose orbital a	ingular momentum is
	equal to an integral multipl		-)1. / 22	1)1. / 2 – 3
1.0	a) $nh/2\pi$	b) $nh \times 2\pi$	c) $nh/2\lambda$	d) $nh/2\pi\lambda$
16.	The gas which was identified	<u> </u>		•
17	a) oxygen	b) hydrogen	c) helium	d) nitrogen
17.	The value of first quantized	•	_	1) 0 0 7 2
10	a) 0.0053 nm	b) 5.3 nm	c) 0.053 nm	d) 0.053 cm
18.	According to Bohr's theory,			
4.0	a) 4 (0.053 nm)	b) 9 (0.053 nm)	c) 16 (0.053 nm)	d) 25(0.053 nm)
19.	The speed of hydrogen electronic speed of hyd			
	a) $2\lambda ke^2/nh$	b) $2\pi ke^2/\lambda h$	c) $2\pi ke^2/nh$	d) $2\pi ke^2/h$
20.	The quantized Bohr orbit rad			2
	a) n^2r_3	b) nr_1	c) n^2r_2	d) n^2r_1
21.	The energy required to comp			
	a) excited energy		c) accelerated energy	d) orbital energy
22.	By the transition of inner she	ell electrons in heavy at	coms, high energy photo	ons are emitted which are
	a) gamma rays	b) X-rays	c) radio waves	d) photon rays
23.	For the production of X-rays	, the electrons which st	trike with the target are	
	a) slow moving	b) fast moving	c) vibrational electron	d) free electrons
24.	The amount of energy requir	red to completely remo	ve an electron from the	first Bohr orbit is

		b) 13.6 eV		d) 1.36 eV
25.	The continuous X-ray spectr			
	a) Braking radiation	,	· · · · · · · · · · · · · · · · · · ·	d) none of a & b
26.	X-rays can penetrate several			
	a) millimeters	,		,
27.			dominate, and allow greater a	amount of incident
	X-rays to pass through them	are		
	a) oxygen, nitrogen, hydrog	gen	b) oxygen, hydrogen, heli	um
	c) oxygen, hydrogen, carbor	1	d) carbon, nitrogen, oxyge	en
28.	CAT is the abbreviation of			
	a) computerized axial topol		b) computerized atomic to	
	c) computerized axial	tomography	d) computerized atomic	tomography
29.	The X-rays emitted in inner	shell transitions are ca	alled as their energy of	depends upon the
	type of target material.			
	a) gamma rays b) spe	ecial X-rays c) Ch	naracteristic X-rays d) cont	inuous X-rays
30.	CAT Scanners can detect de			·
	a) 50 percent			d) 40 percent
31.	Three dimensional CAT Sc			, •
	a) arachnoid cyst			d) chalazia cyst
32.	Dimension of Rydberg cons		,	,
	a) LT ⁻¹	b) L ⁻¹	c) (LT) ⁻¹	d) L ⁻¹ T
33.	Which series lies in the Ultra	/		
	a) Lyman series	_	c) Brackett serie	d) Balmer series
34.	X-rays were discovered by:	,	-,	.,
	a) Roentgen		c) Marie Curie	d) Van Lave
35.	The reverse process of photo			<i>a)</i> + <i>a</i> = <i>a</i> + <i>c</i>
<i>.</i>	a) Annihilation of matter	o creeding current is curre	b) Compton effect	
	c) Pair production		d) X-rays	
36.	The total energy of electron	in the Bohr orbit is giv	,	
20.	a) $- ke^2/2r$			d) - ke^2/r
37.	· · · · · · · · · · · · · · · · · · ·		cound state E_1 , thereby leaving	,
57.	excited state E_2 , is	or of an atom in the gr	Same State 21, thereby leaving	5 me atom m me
	a) spontaneous absorption		b) stimulated absorption	
	c) induced absorption		d) both b & c	
38.	·	tom emits a nhoton of	energy hf = $E_2 - E_1$, in any a	arhitrary direction is
50.	a) Spontaneous emission	tom chints a photon of	b) stimulated emission	diolitary direction is
	c) induced emission		d) both a & c	
39.	Electron can exist in the atom	m but outside the nucl	,	
37.	a) speed of electron is equal		b) speed of electron is more	than speed of light
	c) speed of electron is less that		d) None of these	than speed of fight
40.	The radius of hydrogen ator		d) None of these	
1 0.	a) 5 x 10 ⁻¹¹ m	b) 5 x 10 ⁻¹¹ cm	c) 5 x 10 ⁻¹¹ mm	d) 5 x 10 ⁻¹¹ dm
41.			eed would have to be greater	,
71.	a) 10^{10} cm/s	b) 10 ¹⁰ m/s	c) 10^{20} m/s	d) 10^{20} cm/s
12	·	,	C) 10 III/S	u) 10 cm/s
42.	A typical nucleus is less than a) 10^{10} m	b) 10 ⁻¹⁰ m	c) 10^{14} m	d) 10 ⁻¹⁴ m
12		0) 10 III	c) 10 m	u) 10 III
43.	Lasers are used to produce	~!~4	h) manaahmamatia haama	f wielle le liele
	a) Intense beam of visible light		b) monochromatic beam of	or visible light
4.4	c) coherent beam of visible		d) All of them	t 41
44.		men more atoms are ii	n the lower energy state E ₁ th	an in the excited
	state E_2 , is known as		1.)	
	a) population inversion		b) normal population	
	c) stimulated population		d) atomic population	

45.	In the phenomenon of Las	er production, atom c	an reside in the excited state	only for					
	a) 10^{-6} s	b) 10 ⁻⁷ s	c) 10^{-8} s	d) 10 ⁻⁹ s					
46.	In the phenomenon of Laser production, atom can reside in the meta stable state for								
	a) $\sim 10^{-3} \text{s}$	b) $\sim 10^{-8} \text{s}$	c) $\sim 10^{-4} \text{s}$	d) $\sim 10^{-10}$ s					
47.	Common type of Laser used in physics laboratories is								
	a) hydrogen neon Laser		b) helium-neon Laser	b) helium-neon Laser					
	c) carbon neon Laser		d) argon neon laser						
48.	In Helium-neon Laser disc	In Helium-neon Laser discharge tube, helium gas is							
	a) 15%	b) 85%	c) 75%	d) 35%					
49.	In Helium-neon Laser, in 1	neta stable state, heli	um is located at the energy le	evel:					
	a) 20.66 eV	b) 20.77 eV	c) 20.61 eV	d) 20.71 eV					
50	In Helium-neon Laser discharge tube, neon gas is								
	a) 85%	b) 15%	c) 75%	d) 45%					
51.	Red Laser light has a wavelength of								
	a) 630.8 nm	b) 630 cm	c) 632.8 nm	d) 639.9 nm					
52.	Laser beams can generate three dimensional images of objects in a process called								
	a) polygraphy	b) telegraphy	c) holography	d) autography					
53.	Laser technology has been widely used in the field of								
	a) neurology	b) astrology	c) ophthalmology	d) psychology					
54.	Laser is the acronym for								
	a) Light Amplification by Stimulated Emission of Radiation								
	b) Light Amplification by Spontaneous Emission of Radiation								
	c) Light Amplified by Stimulated Emission of Radiation								
	d) Light Amplification by	Standard Emission of	f Radiation						
55.	X-rays that are emitted in	all directions and with	h a continuous range of frequ	iencies are known as					
	a) characteristic X-rays		b) continuous X-rays						
	c) scattered X-rays		d) stimulated X-rays.						

Answers Key

1	A	11	В	21	В	31	A	41	В	51	C
2	В	12	В	22	В	32	В	42	D	52	C
3	C	13	C	23	В	33	Α	43	D	53	C
4	Α	14	С	24	В	34	Α	44	В	54	Α
5	A	15	A	25	В	35	D	45	C	55	В
6	C	16	C	26	C	36	A	46	Α		
7	D	17	C	27	C	37	D	47	В		
8	В	18	C	28	C	38	D	48	В		
9	В	19	C	29	C	39	C	49	C		
10	C	20	D	30	C	40	A	50	В		

1:	The noble Prize was co	nferred on Glashow, Vin	eberg and Abdus Salam	in:
	(a) 1975	(b) 1977	(c) 1979	(d) 1978
2:	If a nucleus emits an β-	particle along with a neu	trons its mass number re	mains constant but charge decrease
	by:	-		-
	(a) 4	(b) 3	(c) <u>+</u> 2	(d) <u>+</u> 1
3:		was determined by Milli	· · · -	· / -
	(a) 1905	(b) 1895	(c) 1909	(d) 1918
4:	The Υ-rays radiographs		(•) 1505	(4) 1710
	(a) Agricultural industr		(c) Support industry	(d) all of above
5:	PWR Stands for	y (b) Wedicai madsiry	(c) Support madsiry	(d) an or above
5.	(a) Pressurize wind rect	-04	(h) Proggueizo viotor roc	actor
	* /	tOI	(b) Pressurize water rea	ictor
6.	(c) Power wind reactor	d dal . of . t	(d) none of above	
6:		d model of atom, the pos		
	(a) is uniformly spread		(b) Is concentrated at it	
_	(c) is at certain distance		(d) is scattered by an a-	particles
7:		nitrogen with alpha parti		(1) TT
_	(a) Electron	(b) neutron	(c) proton	(d) X-rays
8:		eutron by the study of sc		
	(a) Gold foil	(b) Nitrogen	(c) Beryllium	d) oxygen
9:	Neutron was discovered	d by		
	(a) curie	(b) roentgen	(c) Rutherford	(d) Chadwick
10:	Neutrons and protons in	n the nucleus are together	r called	
	(a) photon	(b) nucleons	(c) mesons	(d) phonons
11:	The Nuclei having the s	same mass number but di	ifferent atomic number a	re called
	(a) isotopes	(b) isobars	(c) isotone	(d) isomers
12:		ne massed of positive ion	s or protons and to detec	t the isotopes is called
	(a) Geiger country			per (d) Aston mass spectrometer
13:	The nucleus (or nuclide		(*)	· · · · · · · · · · · · · · · · · · ·
10.	(a) proton	(b) Triton	(c) Deuterons	(d) positron
14:	Nuclear force exists bet	* /	(c) Beaterons	(a) position
.	(a) neutron-neutron	(b) proton-proton	(c) proton-neutron	(d) All of the above
15:	W +, W - and Z+ boons		(c) proton-neutron	(d) 7 Hi of the above
13.	(a) Electroweak interac		(h) Flootrowaak interes	tion at high anaroy
		tion at low energy	(b) Electroweak interac(d) Gravitational force	tion at high energy
16.	(c) Nuclear forces	of constituent must sug 1		f the menultant mucleus
16:		of constituent nucleons a		
1.7		(b) greater		(d) none of the above
17:	9.	required to break the nuc		(1) P' 1'
10	(a) nuclear	(b) kinetic energy	(c) potential energy	(d) Binding energy
18:	The neutron and proton			
	(a) Positron	(b) Triton	(c) Deuterons	(d) Photons
19:	The binding energy of l			
	(a) 22.24 MeV	(b) 2.224 MeV	(c) 0.224 MeV	(d) 222.4 MeV
20:	Radioactivity was disco	overed by		
	(a) H. Becquerel	(b) J,J, Thomson	(c) Bohr	(d) Madame curie
21:	When a nucleus emits a	and alpha particle, its ato	mic mass drops by	
	(a) 2	(b) 1	(c) 4	(d) 3
22:	The elements showing	radioactivity has atomic:	number 'Z'	
	(a) Z>50	(b) Z<82	(c) $Z > 82$	(d) $Z < 70$
23:	Curie is unit of	•	` ,	. ,
	(a) Conductivity	(b) Binding energy	(c) Resistivity	(d) Radioactivity
24:	β – particles are	(-) 8 8 ,		(1)
	(a) Hydrogen nuclei	(b) Electrons	(c) Protons	(d) Photons
25:	Gamma-rays consist of		(-, 1100010	(4) 2 110101115
- 5.	(a) Electrons	(b) protons	(c) photons	(d) positrons
26:		tegration per unit time)		(a) positions
20.	(a) Is constant	-	creases exponentially wit	h time
	(a) 15 Constant	(0) Dec	reases exponentially wit	

	(c) varies inversely ad t		ecreases linearly with tim	ne
27:	A curie represents a ver	ry strong, source of		
	(a) a – particle	(b) β-particle	(c) Radioactivity	(d) Y-rays
28:	The half-life of a radioa	active element depends	on	•
	(a) Temperature			mount of radio active substance
29:	Capture of a neutron by			
	(a) Deuteron and Υ-ray	•	(b) Deuteron a	and a-rays
	(c) Deuteron and β-rays		(d) Tritron and	
30:				uclei with the release of energy is
30.	_	neavy nucleus is blokel	i into two intermediate ii	uciei with the felease of ellergy is
	called	(1-) 6'	(-) -1	(4) Chamical marking
21	(a) fusion	(b) fission	(c) chain reaction	(d) Chemical reaction
31:	Fission reaction can be	•		(1) 33 11 0
	` '		(c) Fast neutrons	(d) Neither fast nor slow neutrons
32:	_	_	n the basis of liquid drop	by
	(a) Otto Hahn	(b) Lie Meitner (c) Bo	ohr and Wheeler	
	(d) Strassman and Hahr	1		
33:	during fission process,	the average number of r	neutrons produced per fis	sion
	(a) 1	(b) 2	(c) 3	(d) 2.5
34:	Fission chain reaction I	s controlled by introduc	ing	
	(a) Graphite rode	(b) cadmium rods	(c) Iron rods	(d) platinum rods
35:	The moderator used in	a nuclear reactor is		• • •
	(a) Aluminum	(b) sodium	(c) calcium	(d) graphite
36:	In liquid metal fast bree		* /	(1) 8-11-11-1
	(a) $_{92}U^{235}$	(b) $92U^{238}$	(c) $_{92}U^{234}$	(d) $_{92}U^{239}$
37:				h heavier nuclei with release of
57.	energy is called	vo or more fight fluctor	comomic together to form	Theavier nacies with resease of
	(a) Fission	(b) fusion	(c) chain reaction	(d) chemical reaction
38:	Materials can be identif	* *	(c) chain reaction	(d) chemical reaction
36.	(a) Hardness	(b) Density	(c) Mass	(d) Half-life
20.			* /	(u) Haif-life
39:	When an alpha-particle		_	(4) ===:tions
10.	(a) Neutrons	(b) protons	(c) electrons	(d) positions
40:	The range of 7.7 MeV a			(4) 7
4.1	(a) 10 cm	(b) 20 cm	(c) 17 cm	(d) 7 cm
41:	Beta-particle in single e			
	(a) Their small mass		eir small charges and gre	ater speeds
	(c) their smaller energy		eir smaller density	
42:	A 3MeV Beta – particle	_		
	(a) 655 mm	(b) .65 mm	(c) 6.5 mm	(d) 0.065 mm
43:	Gamma-rays are electron	0		
	(a) X-rays	(b) light waves	(c) Heat waves	(d) microwaves
44:	Which one of the follow	ving radiation is extrem	ely penetrating	
	(a) neutrons	(b) Beta-rays	(c) Alpha-rays	(d) Gamma-rays
45:	Pair production can tak	e place only with		
	(a) X-rays	(b) Heat radiation	(c) gamma-rays	(d) ultraviolet rays
46:	Capture of a neutron by	a nucleus results in the		•
	(a) Triton	(b) Radio isotope	(c) deuteron	(d) helium
47:	A device producing ion	•	* /	()
	(a) A betatron	(b) A Geiger counter	(c) A cyclotron	(d) mass spectrograph
48:	Geiger counter is a dev		(·) -J	()
	(a) mass	(b) Momentum	(c) Charge	(d) Nuclear radiation
49:			t fast and operate at low	
т/.	(a) Geiger counter			tor (d) Scintillation counter
50:	The mass of an electror			or (a) Demandion country
50.	(a) 0.00065 u	(b) 0.00055 u	(c) 1.004 u	(d) 0.00075 u
	(a) 0.00000 u	(<i>b)</i> 0.000 <i>33</i> u	(c) 1.00 -1 u	(u) 0.00013 u